



FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #20628Generic Copy

Issue Date: 27-Aug-2014**TITLE:** Wafer size change (5inch to 6inch) at ON Semiconductor fab location in Niigata, Japan.**PROPOSED FIRST SHIP DATE:** 02-Dec-2014 or earlier upon customer approval**AFFECTED CHANGE CATEGORY(S):** Wafer size change**FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:**

Contact your local ON Semiconductor Sales Office or

<Akio.Nagahama@onsemi.com> <Minoru.Akaishi@onsemi.com>

<Yukihisa.Kumagai@onsemi.com> <Yoshinori.Naito@onsemi.com>

SAMPLES: Contact your local ON Semiconductor Sales Office or

<Yoshinori.Naito@onsemi.com>

<Tetusya.Ishizuka@onsemi.com> <Akio.Nagahama@onsemi.com>

ADDITIONAL RELIABILITY DATA: Available

Contact your local ON Semiconductor Sales Office or

<Satoru.Fujinuma@onsemi.com>

<Yukihisa.Kumagai@onsemi.com>

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>.

DESCRIPTION AND PURPOSE:

This is to increase our supply capacity to support increased demand. Thus to be able to continuously supply products, Wafer size will be changed from 5inch to 6inch for parts identified in this FPCN.



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RELIABILITY DATA SUMMARY:

Reliability Test Results:

Package name: SIP4/SIP4J

Test Items	Test Condition	Test Time	Sample Size	Failure
Steady State Operating Life	Tj=165C, Vcc1=24V, Vcc2=about7V(8A), Input=16.7Hz(duty5%)	2000h	22	0
Temperature Humidity Bias	Ta=85C,RH=85%, Vcc1=24V, Vcc2=about7V 1h/3h=on/off	1000h	22	0
Temperature Humidity Storage	Ta=85C,RH=85%	1000h	22	0
Temperature Cycle	Ta=-65C 30min. ⇔ Ta=165C 30min.	600cyc	22	0
Pressure Cooker	Ta=121C,RH=100% ,2.03x10 ⁵ Pa	100h	22	0
High Temperature Storage	Ta=165C	2000h	22	0
Low Temperature Storage	Ta=-55C	1000h	22	0
Electrostatic Discharge(HBM)	Vcc pin versus each pin, Gnd pin versus each pin C=100pF, R=1500ohm, V=+/-2000V	3times	3	0
Electrostatic Discharge(MM)	Vcc pin versus each pin, Gnd pin versus each pin C=200pF, R=0ohm, V=+/-200V	3times	3	0

Note Judgment Criteria: Judgment Criteria are due to the drift judgment of the electrical characteristics in the detail specification.

ELECTRICAL CHARACTERISTIC SUMMARY:

There is no change in the electrical performance. Datasheet specifications remain unchanged.

CHANGED PART IDENTIFICATION:

Affected products will be identified with date code.

List of affected Parts:

LA9900U-N-E
LA9901U-N-E
LA9902U-N-E
LA9903U-N